PRODUCT DATA SHEET

To learn more about JGSEMI, please visit our website at

Datasheet Resources Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.

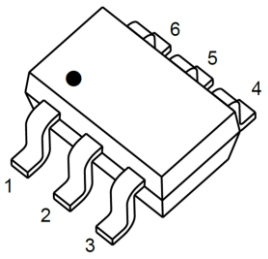
CJ3134KDW

20V Dual N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	190mΩ@4.5V	0.75A
	260mΩ@2.5V	
	390mΩ@1.8V	

SOT-363



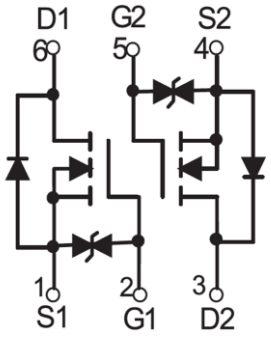
Feature

- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Schematic diagram



ABSOLUTE MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current(1)	I_D	0.75	A
Power Dissipation(1)	P_D	150	mW
Thermal Resistance from Junction to Ambient(1)	$R_{\theta JA}$	833	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS(T_a=25℃ unless otherwise noted)

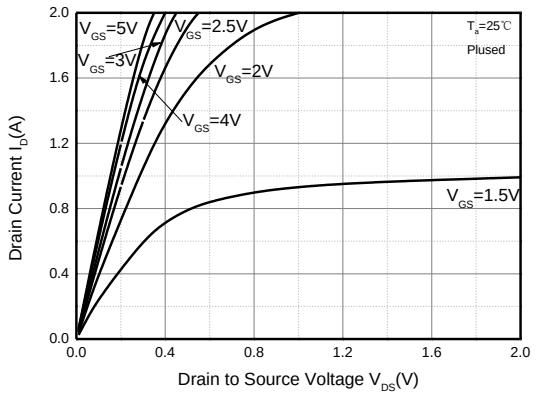
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =20V,V_{GS} = 0V			1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±10V, V_{DS} = 0V			±20	μA
Gate threshold voltage(1)	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.35	0.75	1.1	V
Drain-source on-resistance(1)	$R_{DS(on)}$	V_{GS} =4.5V, I_D =650mA		190	260	mΩ
		V_{GS} =2.5V, I_D =550mA		260	360	
		V_{GS} =1.8V, I_D =450mA		390	590	
Forward tranconductance(1)	g_{FS}	V_{DS} =10V, I_D =800mA		1.6		S
Dynamic characteristics(2)						
Input Capacitance	C_{iss}	V_{DS}=16V,V_{GS}=0V,f=1MHz			120	pF
Output Capacitance	C_{oss}				20	
Reverse Transfer Capacitance	C_{rss}				15	
Switching Characteristics(2)						
Turn-on delay time	$t_{d(on)}$	V_{DS}=10V,I_D=500mA, V_{GS}=4.5V,R_G=10Ω		6.7		ns
Turn-on rise time	t_r			4.8		
Turn-off delay time	$t_{d(off)}$			17.3		
Turn-off fall time	t_f			7.4		
Source-Drain Diode characteristics						
Diode Forward voltage(1)	V_{DS}	I_S=0.15A, V_{GS} = 0V			1.2	V

Notes:

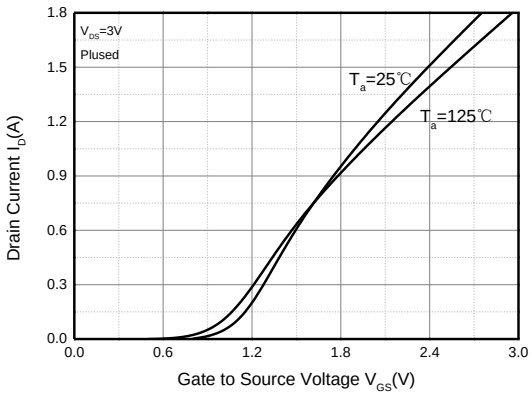
1. Pulse Test : Pulse width≤300μs, duty cycle≤0.5%.
2. Guaranteed by design, not subject to production testing

Typical Electrical and Thermal Characteristics

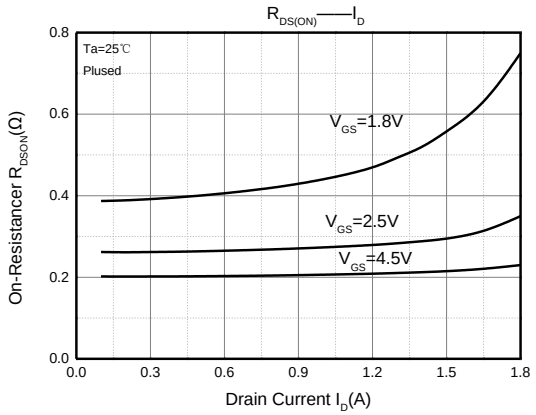
Output Characteristics



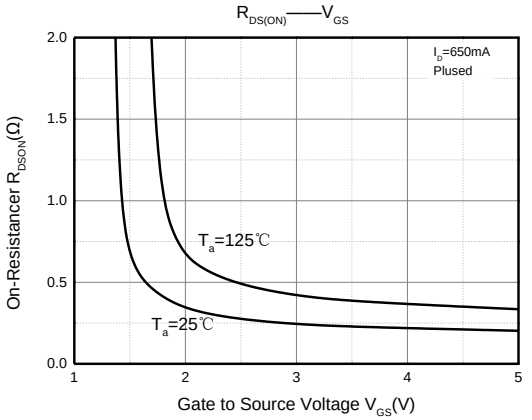
Transfer Characteristics



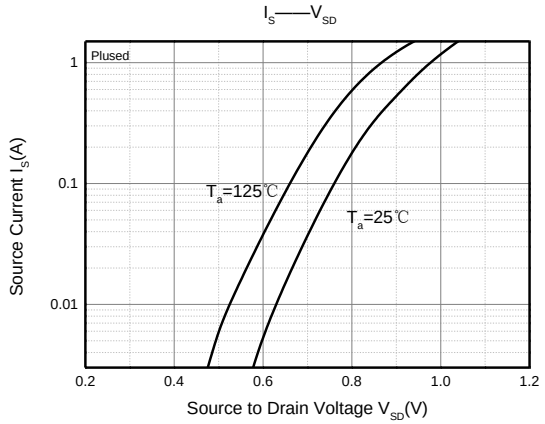
$R_{DS(ON)}$——I_D



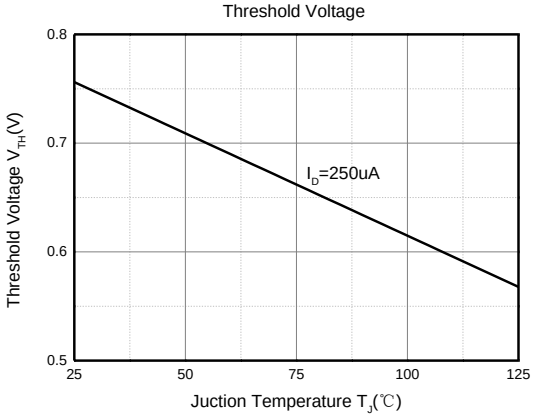
$R_{DS(ON)}$——V_{GS}



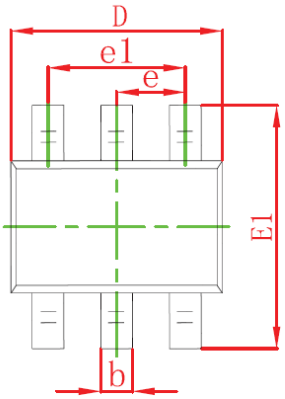
I_S——V_{SD}

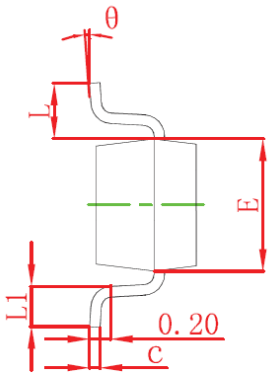


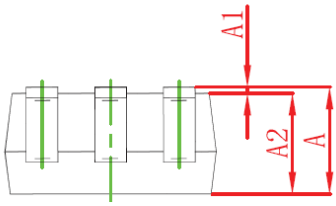
Threshold Voltage



SOT-363 Package Information







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.100	0.150	0.004	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.400	0.085	0.094
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

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